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<u>Diodes Incorporated</u> <u>DMP3018SFK-7</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Datasheet of DMP3018SFK-7 - MOSFET P-CH 30V 10.2A DFN2523-6

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)max}	I _D T _A = +25°C
-30V	14.5mΩ @ V_{GS} = -10 V	-10.2A
-307	$25.5 \text{m}\Omega$ @ $V_{GS} = -4.5 \text{V}$	-7.7A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- DC-DC Converters

Features and Benefits

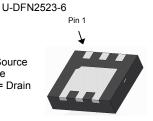
- Low On-Resistance
- Low Input Capacitance
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

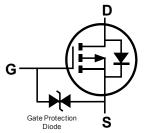
- Case: U-DFN2523-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.008 grams (Approximate)



Pin 1, 2 = Source Pin 3 = Gate Pin 4, 5, 6 = Drain



Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3018SFK-7	U-DFN2523-6	3,000/Tape & Reel
DMP3018SFK-13	U-DFN2523-6	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2523-6





P7 = Product Type Marking Code 7P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2014	1	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D		Ξ	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage			V _{GSS} ±25		V
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	-10.2 -8.1	А		
Continuous Drain Current (Note 6) V _{GS} = -4.5V	ID	-7.7 -6.1	А		
Maximum Continuous Body Diode Forward Current (N	I _S	-3	Α		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-80	Α		
Avalanche Current (Note 7)	I _{AS}	-14	Α		
Avalanche Energy (Note 7)	Eas	104	mJ		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	123	°C/W
Total Power Dissipation (Note 6)		P _D	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	55	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	17	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	7.2	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	•		•	•			
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V$, $I_D = -10mA$	
Zero Gate Voltage Drain Current T _J = +25°C	1	_	_	-1	μA	V _{DS} = -24V, V _{GS} = 0V	
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)	I _{DSS}	_	_	-100	μΑ	$V_{DS} = -24V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	-1	-1.6	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D	_	9.5	14.5	mΩ	$V_{GS} = -10V, I_D = -9.5A$	
Static Dialii-Source On-Resistance	R _{DS(ON)}	_	15	25.5	11152	$V_{GS} = -4.5V$, $I_D = -6.9A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V$, $I_S = -1A$	
On State Drain Current (Note 9)	I _{D(ON)}	-20	_	_	Α	V _{DS} ≦5V, V _{GS} = -10V	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	2,207	4,414		V - 45V V - 0V	
Output Capacitance	Coss	_	390	780	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	343	686		1 - 1101112	
Gate Resistance	Rg	_	8.4	20	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -10V)	Qg	_	42.7	90			
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	21.6	45	nC	V - 15V I - 0.5A	
Gate-Source Charge	Qgs	_	7.9	16	IIC	$V_{DS} = -15V, I_{D} = -9.5A$	
Gate-Drain Charge	Q _{gd}	_	10	20			
Turn-On Delay Time	t _{D(on)}	_	7.35	15			
Turn-On Rise Time	tr	_	16.4	30		$V_{DD} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(off)}	_	67.2	110	ns	$R_{GEN} = 6\Omega$, $I_{D} = -9.5A$	
Turn-Off Fall Time	t _f	_	37.5	60			
Reverse Recovery Time	t _{rr}	_	18.6	35	ns	1 - 0 5 4 3 3 4 5 - 400 4 6 -	
Reverse Recovery Charge	Q _{rr}	_	8.6	17.5	nC	I _S = -9.5A, di/dt = 100A/μs	

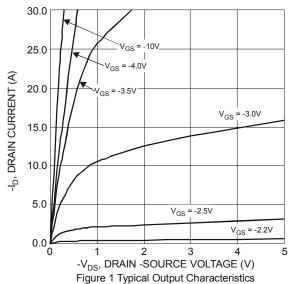
Notes:

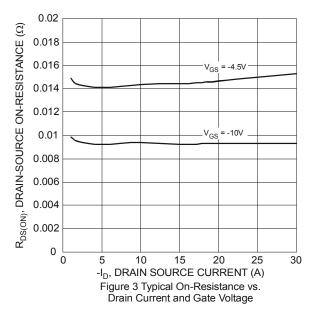
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 7. UIS in production with L = 1mH, T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.

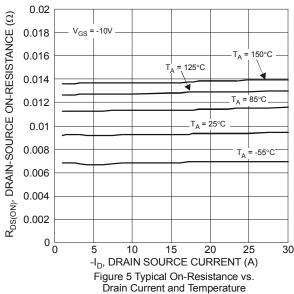
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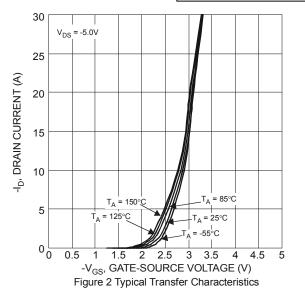


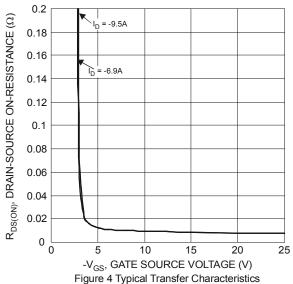






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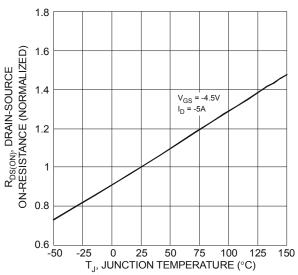


Figure 6 On-Resistance Variation with Temperature



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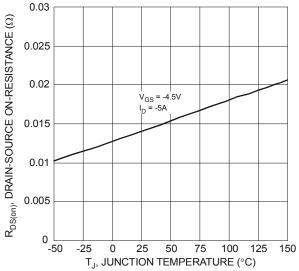


Figure 7 On-Resistance Variation with Temperature

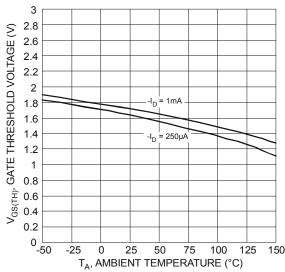
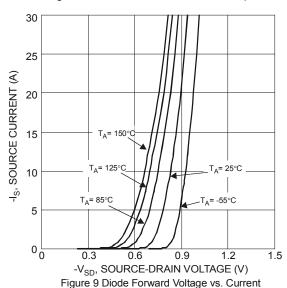
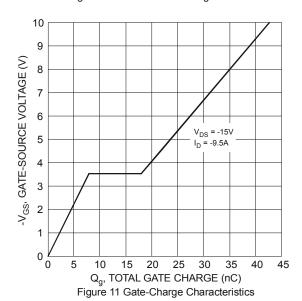
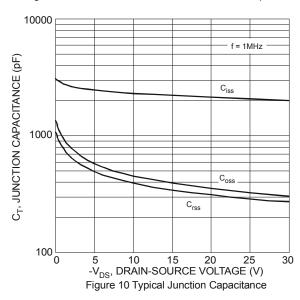
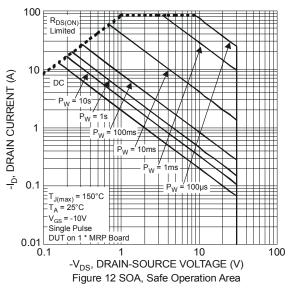


Figure 8 Gate Threshold Variation vs. Ambient Temperature







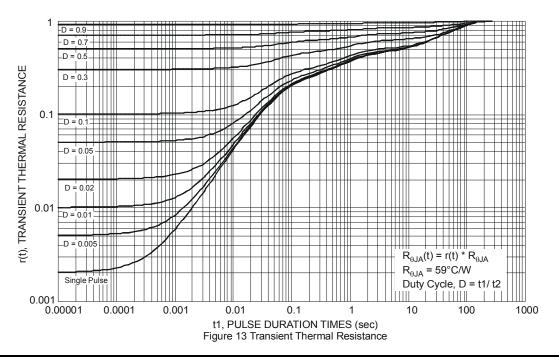


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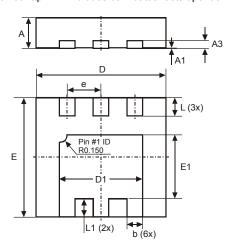


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Package Outline Dimensions

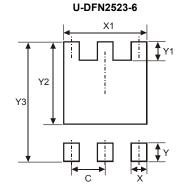
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2523-6							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0	0.05	0.02				
A3	-	-	0.152				
b	0.25	0.35	0.30				
D	2.45	2.55	2.50				
D1	1.55	1.65	1.60				
е	_	_	0.65				
Е	2.25	2.35	2.30				
E1	1.18	1.28	1.23				
L	0.30	0.40	0.35				
L1	0.30	0.40	0.35				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	1.700
Υ	0.650
Y1	0.450
Y2	1.830
Y3	2.700



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